

SMTPB SERIES

TRISILTM

MAIN APPLICATIONS

Any sensitive equipment requiring protection against lightning strikes:

- ANALOG AND DIGITAL LINE CARDS
- MAIN DISTRIBUTION FRAMES
- TERMINALS AND TRANSMISSION EQUIPMENT
- GMS-TUBE REPLACEMENT

DESCRIPTION

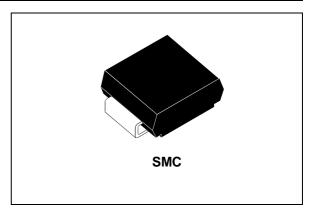
The SMTPBxx series has been designed to protect telecommunication equipment against lightning and transient induced by AC power lines.

FEATURES

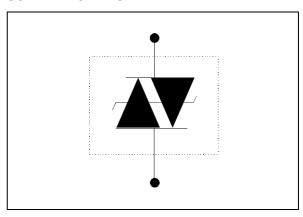
- BIDIRECTIONAL CROWBAR PROTECTION.
- BREAKDOWN VOLTAGE RANGE: From 62 V To 270 V.
- HOLDING CURRENT: I_H = 150 mA min
- REPETITIVE PEAK PULSE CURRENT : IPP = 100 A, 10/1000 µs.

BENEFITS

- NO AGEING AND NO NOISE
- IF DESTROYED, THE SMTPB FALLS INTO SHORT CIRCUIT, STILL ENSURING PROTECTION



SCHEMATIC DIAGRAM



COMPLIES WITH THE FOLLOWING STANDARDS:	Peak Surge Voltage (V)	Voltage Waveform (μs)	Current Waveform (μs)	Admissible lpp (A)	Necessary Resistor (Ω)
CCITT K20	4000	10/700	5/310	100	-
VDE0433	4000	10/700	5/310	100	-
VDE0878	4000	1.2/50	1/20	100	-
IEC-1000-4-5	level 4 level 4	10/700 1.2/50	5/310 8/20	100 100	-
FCC Part 68, lightning surge type A	1500 800	10/160 10/560	10/160 10/560	200 100	
FCC Part 68, lightning surge type B	100	5/320	5/320	25	-
BELLCORE TR-NWT-001089 First level	2500 1000	2/10 10/1000	2/10 10/1000	500 100	-
BELLCORE TR-NWT-001089 Second level	500	2/10	2/10	500	-
CNET I31-24	4000	0.5/700	0.8/310	100	-

October 1998 - Ed: 2C 1/5

SMTPBxxx

ABSOLUTE MAXIMUM RATINGS $(T_{amb} = 25^{\circ}C)$

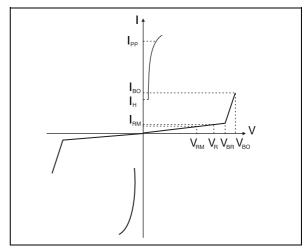
Symbol	Parameter	Value	Unit	
Р	Power dissipation	T _{lead} = 50 °C	5	W
Ірр	Peak pulse current	10/1000 μs 8/20 μs 2/10 μs	100 250 500	A
I _{TSM}	Non repetitive surge peak on-state current	tp = 20 ms	50	А
dV/dt	Critical rate of rise of off-state voltage	V_{RM}	5	KV/μs
T _{stg} T _j	Storage temperature range Maximum junction temperature		- 55 to + 150 + 150	သိ သိ
TL	Maximum lead temperature for soldering	+ 260	°C	

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-l)	Junction to leads	20	°C/W
R _{th} (j-a)	Junction to ambient. On printed circuit with standard footprint dimensions.	75	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
V_{RM}	Stand-off voltage
I _{RM}	Leakage current at stand-off voltage
V_R	Continuous Reverse voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
lΗ	Holding current
I _{BO}	Breakover current
I _{PP}	Peak pulse current
С	Capacitance



Туре	Marking	IRM @ VRM		I _R @ V _R		Vво @ І во		Ін	С
		max.		max. note1		max. note2	max.	min. note3	typ. note4
	Laser	μΑ	٧	μΑ	٧	٧	mA	mA	pF
SMTPB62 SMTPB68 SMTPB120 SMTPB200 SMTPB270	W07 W11 W21 W31 W43	2 2 2 2 2	56 61 108 180 243	50 50 50 50 50	62 68 120 200 270	82 90 160 267 360	800 800 800 800 800	150 150 150 150 150	160 160 140 130 120

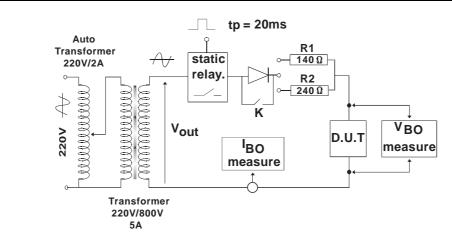
All parameters tested at 25°C, except where indicated.

Note 3: See test circuit 2.

Note 4: $V_R = 1V$, F = 1MHz. Refer to fig 3 for C versus V_R .

2/5

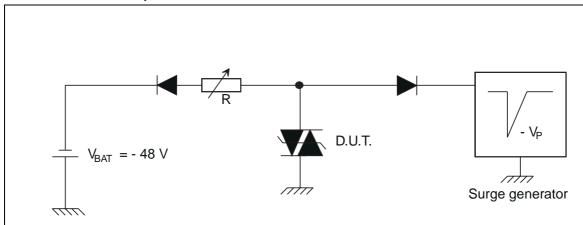
TEST CIRCUIT 1 FOR I_{BO} and V_{BO} parameters :



TEST PROCEDURE:

- Pulse Test duration (tp = 20ms):
 - For Bidirectional devices = Switch K is closed
 - For Unidirectional devices = Switch K is open.
- Vour Selection
 - Device with $V_{\mbox{\footnotesize{BO}}}$ < 200 Volt
 - Vout = 250 V_{RMS}, R_1 = 140 Ω .
 - Device with V_{BO} ≥ 200 Volt
 - Vout = 480 V_{RMS}, R_2 = 240 Ω .

TEST CIRCUIT 2 for I_H parameter.



This is a GO-NOGO Test which allows to confirm the holding current (IH) level in a functional test circuit.

TEST PROCEDURE:

- 1) Adjust the current level at the I_H value by short circuiting the AK of the D.U.T.
 - 2) Fire the D.U.T with a surge Current : lpp = 10A , 10/1000 μ s. 3) The D.U.T will come back off-state within 50 ms max.

Fig. 1: Non repetitive surge peak on-state current versus overload duration (Tj initial=25°C).

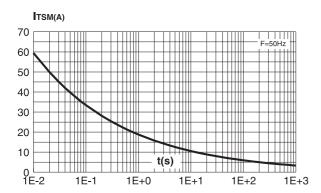


Fig. 2: Relative variation of holding current versus junction temperature.

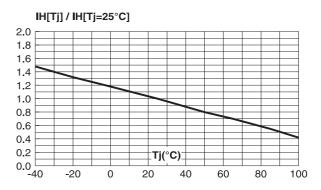
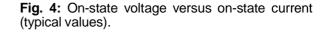
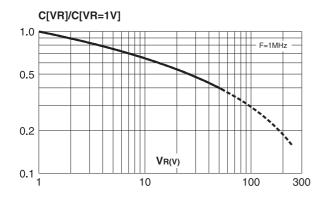


Fig. 3: Relative variation of junction capacitance versus reverse applied voltage(typical values). Note: For V_{RM} upper than 56V, the curve is extrapolated (dotted line).





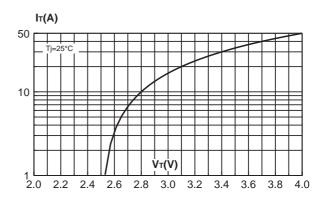
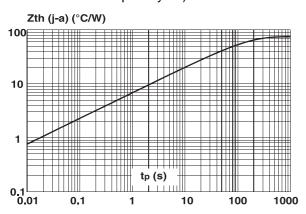
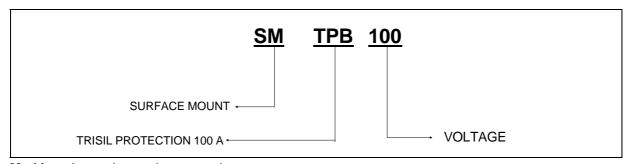


Fig. 5: Transient thermal impedance junction to ambient versus pulse duration (for FR4 PC Board with recommended pad layout).



4/5

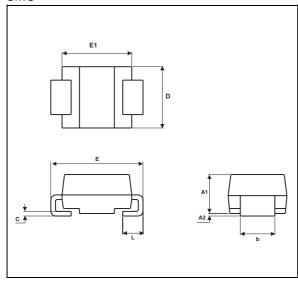
ORDER CODE



Marking: Logo, date code, type code.

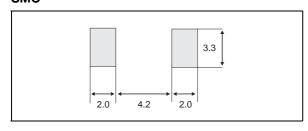
PACKAGE MECHANICAL DATA.

SMC



	DIMENSIONS							
REF.	Mi	llimete	ers	Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
A1	2.40	2.70	3.00	0.094	0106	0.118		
A2	0.05		0.20	0.002		0.008		
b	2.90		3.10	0.114		0.122		
С	0.29		0.32	0.011		0.013		
E1	6.30	6.40	6.60	0.248	0.252	0.260		
D	4.80	5.00	5.20	0.189	0.197	0.205		
Е	7.60	7.80	8.00	0.299	0.307	0.315		
L	1.30		1.70	0.051		0.067		

FOOTPRINT DIMENSIONS (in millimeters) **SMC**



Packaging: Standard packaging is in tape and reel **Weight**: 0.269g.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 1998 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

http://www.st.com

